TITLE:
Reduction of doping and trap concentrations in 4H-SiC epitaxial layers grown by chemical vapor deposition

AUTHOR(S):
Kimoto, Tsunenobu; Nakazawa, Satoshi; Hashimoto, Koichi; Matsunami, Hiroyuki

CITATION:

ISSUE DATE:
2001-10-22

URL:
http://hdl.handle.net/2433/24206

RIGHT:
Copyright 2001 American Institute of Physics. This article may be downloaded for personal use only. Any other use requires prior permission of the author and the American Institute of Physics.
Reduction of doping and trap concentrations in 4H–SiC epitaxial layers grown by chemical vapor deposition

Tsunenobu Kimoto, Satoshi Nakazawa, Koichi Hashimoto, and Hiroyuki Matsunami
Department of Electronic Science and Engineering, Kyoto University, Yoshidahommachi, Sakyo, Kyoto 606-8501, Japan

(Received 2 May 2001; accepted for publication 17 August 2001)

High-purity and thick 4H–SiC(0001) epilayers have been grown by a horizontal hot-wall chemical vapor deposition (CVD) system, which was designed and built at the authors’ group. The background donor concentration has decreased by reducing pressure during CVD, and a low donor concentration of \(1 \times 10^{12} \text{ cm}^{-3}\) was achieved by CVD growth at 80 Torr. The free exciton peaks dominated in low- and room-temperature photoluminescence spectra without titanium or point-defect related peaks. The electron mobility reaches 981 cm\(^2\)/V s at room temperature and 46 200 cm\(^2\)/V s at 42 K. The total trap concentration could be reduced to \(4.7 \times 10^{11} \text{ cm}^{-3}\) by increasing the input C/Si ratio. © 2001 American Institute of Physics. [DOI: 10.1063/1.1413724]

Through recent progress in silicon carbide (SiC) growth and device processing technologies, high-voltage (300 and 600 V) 4H–SiC Schottky diodes have been realized as commercial products.\(^1\) The major advantages of SiC Schottky diodes, a unipolar device, include fast switching speed and negligibly small switching loss, owing to the absence of injected minority carriers. Although the theoretical specific on-resistance of SiC unipolar devices is more than two orders of magnitude lower than that of Si devices,\(^2,3\) the on-resistance becomes unacceptably high for several kilovolts (>3–5 kV) SiC unipolar devices. For such high-voltage applications, SiC bipolar devices have promise, owing to the effect of conductivity modulation. In order to fabricate 5 kV SiC bipolar devices, for example, lightly doped (<\(2 \times 10^{13} \text{ cm}^{-3}\)) and thick (>40 \(\mu\text{m}\)) SiC epilayers with a sufficiently long minority carrier lifetime (>1 \(\mu\text{s}\)) are required. On the other hand, thick SiC crystals with ultrahigh purity and low trap concentration are of scientific importance for characterization of intrinsic or defect-related properties.

Chemical vapor deposition (CVD) has been a standard technique to produce device-quality SiC epilayers.\(^3\) The background doping concentration of SiC epilayers has been reduced to \(0.7–2 \times 10^{14} \text{ cm}^{-3}\) either by utilizing the site-competition concept\(^4\) or by employing hot-wall type reactors.\(^5–8\) Although an exceptionally low doping concentration of \(2 \times 10^{13} \text{ cm}^{-3}\) has been recently reported for 4H–SiC epilayers grown at high growth rates by a vertical radiant-heating reactor,\(^9\) the deep level concentration is in the same order as the doping concentration. In this letter, the authors describe the homoepitaxial growth of 4H–SiC(0001) by a home-made hot-wall CVD system. The lowest doping and deep level concentrations are simultaneously achieved.

A hot-wall CVD technique has been demonstrated to grow high-quality and thick SiC epilayers,\(^5,7\) and its prototype CVD system is commercially available. The authors of this letter, however, designed and built a horizontal hot-wall CVD reactor, with which these experimental works have been done. Although the susceptor configuration used in this study is similar to that previously reported,\(^6\) special care was paid to the purity of SiC-coated susceptor and thermal insulator as well as to the susceptor design. The susceptor is 100 mm long and has a gas flow channel with a height of approximately 10 mm. A single 2 in. wafer can be loaded in this system, but in the present work, small pieces (5–10 mm \(\square\)) cut from 8° off-axis 4H–SiC(0001) wafers were used. Source gases were SiH\(_4\) and C\(_3\)H\(_8\) with a H\(_2\) carrier gas purified by a Ag–Pd cell. After loading substrates and pumping down to \(10^{-6}\) Torr, the CVD process, consisting of \(\text{in situ}\) etching and epitaxial growth, has started. The susceptor temperature was kept at 1500 °C during the \(\text{in situ}\) etching and epitaxial growth. The typical flow rates of SiH\(_4\), C\(_3\)H\(_8\), and H\(_2\) were 1.5 sccm, 0.75 sccm, and 5.0 slm, respectively, if not specified. Most CVD growth runs were carried out at reduced pressure in the range from 60 to 240 Torr, at which a growth rate of 5 \(\mu\text{m/h}\) was obtained under the typical condition. Typical growth time was 5–10 h, by which 25–50 \(\mu\text{m}\) thick epilayers were produced. The details of growth kinetics such as growth rate and surface morphological defects will be published elsewhere,\(^11\) and this letter shall focus on the characterization of epilayers.

Figure 1 shows the donor concentration of unintentionally doped epilayers versus the reactor pressure during CVD. The net donor concentration was determined by

![FIG. 1. Pressure dependence of donor concentration for unintentionally doped epilayers. The donor concentration was determined by C–V characteristics of 1.5 mm\(\times\)6 Ni/4H–SiC Schottky structure processed on 30–50 \(\mu\text{m}\) thick epilayers grown on highly doped \(n\)-type substrates.](https://repository.kulib.kyoto-u.ac.jp)
capacitance–voltage (C–V) measurements on 1.5 mmφ Ni/4H–SiC Schottky structure with 30–50 μm thick undoped epilayers grown on highly doped n-type substrates. The donor concentration showed a significant decrease by reducing the pressure. Preliminary experiments on intentional nitrogen doping have also indicated that the doping efficiency of nitrogen is suppressed at low pressure, in agreement with previous reports. A probable reason for this effect might be the enhanced desorption of nitrogen from the growing surface at reduced pressure. In the present growth system, the reproducible donor concentration is 1–3×10¹⁵ cm⁻³ by CVD growth at 80 Torr, and the lowest value obtained so far is 7×10¹² cm⁻³, which are about one-order-of-magnitude lower than typical values reported from several groups. In addition to the growth at low pressure, the use of pure susceptor and graphite thermal insulator may contribute to the reduction of unwanted impurities. The authors of this letter suggest that the doping concentration was not very sensitive to the C/Si ratio or to the gas flow rates, though the mechanism is not clear at present.

The 4H–SiC epilayers showed smooth surfaces, and the surface defect density was in the range of 100–300 cm⁻². In atomic force microscopy analyses, no macrostep formation was observed for 30–50 μm thick epilayers, leading to a small surface roughness of 0.2 nm. High-resolution x-ray diffraction measurements revealed that the full width at half maximum of the 4H–SiC(0004) peak (2θ=35.6°) in a rocking curve (ω scan) was as small as 9.0 arcs.

Figure 2 represents the photoluminescence (PL) spectra at several temperatures from 4 to 300 K obtained from a 50 μm thick undoped 4H–SiC epilayer grown at 80 Torr. PL peaks such as aluminum-bound exciton (4Al₀ at 3.249 eV), Ti (C₀ at 2.790 eV), and D₁ center (L₁ at 2.902 eV) were not observed. After thermal quenching of the P series at 20 K and the Q series at 50 K (not shown), free exciton peaks govern the PL spectra. The free exciton peaks exhibited longer tails towards the high-energy side with increasing temperature, due to the increase of kinetic energy of free excitons.

Hall effect measurements were performed on a 20 μm thick 4H–SiC epilayer grown on a semi-insulating substrate. The epilayer was intentionally doped with nitrogen to 1.5×10¹⁴ cm⁻³ in order to ensure the formation of Ni ohmic contacts. The sample was 5×5 mm² in size and was processed into a clover-leaf structure by reactive ion etching with CF₄+O₂ gases. The free electron concentration was 1.1×10¹⁴ cm⁻³ at room temperature. Figure 3 shows the temperature dependence of electron mobility for this lightly doped 4H–SiC epilayer. In the mobility calculation, a Hall scattering factor of unity was assumed. In Fig. 3, solid circles and open triangles denote the data measured at the authors’ group and University of Erlangen, respectively. The agreement is very good between the two measurement systems. A high mobility of 981 cm²/V s was obtained at room temperature, and it reaches 46 200 cm²/V s at 42 K, indicating very small impurity scattering. This value is a very high mobility measured in SiC polytypes determined by the Hall effect.

Figure 4 represents the deep level transient spectroscopy (DLTS) spectra for 30 μm thick 4H–SiC epilayers grown
with C/Si ratios of 1.0, 1.2, and 1.5, respectively. All the epilayers were grown at 80 Torr with a growth rate of 5 μm/h, and have a donor concentration of 5–6×10^{13} cm^{-3}. The DLTS signals were taken from 1.5 mm Ni/4H–SiC structure. The reverse bias and pulse voltages applied during DLTS measurements were −5 V and 5 V, respectively. Under this measurement condition, a 10–12 μm deep region from the surface was monitored. The DLTS spectra exhibited two clear peaks at 170 K (trap 1) and 300 K (trap 3). At the lower-temperature flank of the peak for trap 3, a small shoulder is observed. This shoulder (trap 2) was analyzed after subtracting the component of trap 3. Table I summarizes the trap parameters estimated from the Arrhenius plots of emission time constants for the traps 1, 2, and 3, assuming temperature-independent capture cross sections. The activation energies for three traps were determined to be 0.35, 0.52, and 0.65 eV. From the activation energies and capture cross sections, the observed deep levels can be assigned to the ID_{4}, ID_{9}, and Z_{1} centers, as shown in Table I.

By increasing the C/Si ratio from 1.0 to 1.5, the total deep level concentration could be reduced from 9.5×10^{11} to 4.7×10^{11} cm^{-3}, which is one order of magnitude lower than typical concentrations reported (4–20×10^{12} cm^{-3}). In particular, the generation of the Z_{1} center, the major trap, could be suppressed by increasing the C/Si ratio. Although the authors of this letter prepared nitrogen-doped epilayers with donor concentrations up to 5×10^{14} cm^{-3}, as well as epilayers grown at various growth rates from 1.5 to 6.2 μm/h, DLTS measurements on these samples revealed no clear correlation between the trap concentrations and doping concentration or growth rate. As shown in Fig. 4, the growth under C-rich conditions is a key factor to obtain the lower Z_{1}-center concentration. All the defect centers observed in this study are believed to be intrinsic defect complexes, which do not contain specific impurities, but the exact defect structures have not been identified yet. The present study implies that a Si antisite (Si_{C}) or C vacancy (V_{C}), which may be easily created under Si-rich conditions, might be included in the Z_{1} center. DLTS measurements were also made at 300–550 K in the long transient-time range from 20 ms to 2 s, but no deep level signals were detected. Thus, the authors of this letter conclude that the concentration of deep levels located in the range from E_{C} = 0.7 to E_{C} = −1.3 eV (E_{C}: the conduction band edge) may be lower than 5×10^{10} cm^{-3}, assuming a capture cross section of 1×10^{-15} cm^{2}.

In summary, high-purity and thick 4H–SiC(0001) epilayers were grown by horizontal hot-wall CVD. A typical growth rate was 5 μm/h at 1500°C under a pressure of 80 Torr. The background donor concentration exhibited a significant decrease by reducing the reactor pressure, and a low donor concentration of 1–3×10^{13} cm^{-3} was achieved at 80 Torr. The free exciton peaks dominated in low- and room-temperature PL spectra without Ti or point-defect related peaks. High electron mobilities of 981 cm^{2}V^{-1}s^{-1} at room temperature and 46 200 cm^{2}V^{-1}s^{-1} at 42 K were obtained by Hall effect measurements. DLTS analyses revealed three types of deep levels, the Z_{1} center being dominant. The total deep level concentration could be reduced to 4.7×10^{11} cm^{-3} by increasing the C/Si ratio to 1.5.

The authors express deep gratitude to Dr. G. Pensl and M. Laube at the University of Erlangen–Nürnberg for their Hall effect measurements. This work was supported by a Grant-in-Aid for Specially Promoted Research (No. 09102009) from the Ministry of Education, Science, Sports, and Culture of Japan, and also by NEDO. Kyoto University Venture Business Laboratory is also acknowledged for the use of characterization systems.